Doping Dependence of the Pseudogap State in the ab-plane IR Response of La_{2 x}Sr_xCuO₄

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(June 10, 1997, subm itted to Phys. Rev. B)

The ab-plane optical spectra of two single crystals of La_{2 x} Sr_xCuO₄, one underdoped and one overdoped were investigated. We observe a gap-like depression of the elective scattering rate 1= (!;T) below 700 cm⁻¹ in both system s. This feature persists up to 300 K in the underdoped sample with the concentration of Sr x= 0.14 but loss prominance at temperatures above 300 K in the overdoped regime (x= 0.22). Below 700 cm⁻¹ 1= (!;T) is temperature dependent and superlinear in frequency for both samples. Above this frequency the elective scattering rate becomes linear in frequency and is temperature independent in the case of the underdoped La_{1:86}Sr_{0:14}CuO₄ up to 300 K. On the other hand, the overdoped La_{1:78}Sr_{0:22}CuO₄ shows a 1= (!;T) temperature dependence above 700 cm⁻¹ at all temperatures. This behaviour of the frequency and temperature dependent scattering rates is a signature of a pseudogap state in other materials and suggests that both the under and overdoped single-layer HTSC system s La_{2 x} Sr_xCuO₄ have a pseudogap at temperatures exceeding 300 K.

Right from the discovery of high-tem perature superconductivity (HTSC) in the complex copper oxides, it has been recognized that the CuO₂ planes play an important role in the nature of this phenom enon. W hile all of the cuprates share this structural element, La_{2 x} Sr_xCuO₄ (LSCO) possesses only one CuO₂ plane per unit cell which makes it an excellent prototype system for exam ining the role played by the CuO₂ planes. It is also a good model for the study of doping dependence since it can doped by the addition of strontium over a wide range: from the underdoped, where T_c increases with Sr content, to the optim ally doped where T_c reaches its maximum value of 40 K, and to the overdoped region where T_c ! 0 at x = 0:34.¹

It is well known that the in-plane transport properties of HTSC materials are anom abous. For example, the in-plane dc resistivity, $_{ab}(T)$, for the samples doped close to the optim al doping level, is linear in temperature from the superconducting transition temperature T_c to well above 900 K. At the same time, underdoped samples show a crossover from the linear T dependence to a superlinear, $_{ab}(T) = T^{1+}$, below a characteristic temperature T. It was shown by B. Batlogg et al.¹ that T decreases from 800 K to approximately 300 K as the doping level is increased from the strongly underdoped to just over the optim al doping level. Sim ilar behavior at T = T has been observed in the Halle ect coe cient and the magnetic susceptibility.^{2;3}

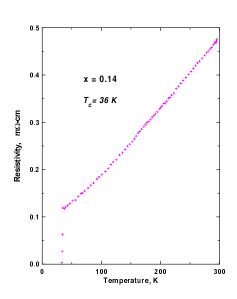
A completely satisfactory m icroscopic understanding of the peculiar transport properties of HTSC is m issing at this time. However, the temperature and doping de-

pendences of the crossover behaviour at T = T noted in the dc transport properties are in accord with the idea that a pseudogap form s in the spectrum of the low -energy electronic excitations responsible for the scattering of the charge carriers. A sim ilar gap-like feature has been observed experim entally in the nuclearm agnetic resonance $(NMR)^4$, the angular resolved photoem ission $(ARPES)^5$, speci cheat and the infrared optical $^{7\,\{9\}}$ (IR) measurements. All of these observations can be consistently interpreted in terms of a pseudogap. In this picture the dc transport properties and the gap form ation are intimately related: a gap in the density of states near the Ferm i level will result in a reduced 1/ (!; T) in the tem perature and spectral region where this gap occurs. Since the ARPES results suggest that the gap has a $d_{x^2 \ v^2}$ m om entum dependence, m om entum -averaging m easurement techniques, like NMR or IR optical, would observe a pseudogap rather than a full gap even at low est tem peratures where this gap is fully form ed.

A pseudogap feature was observed in the c-axis IR conductivity in YBa₂Cu₃O_{7 x} (Y123) and YBa₂Cu₄O₈ (Y124) m aterials.^{7;10} The ab-plane results show increased coherence (a narrow er D rude peak) upon entering the pseudogap state while the c-axis optical response shows a depressed conductivity. The pseudogap state is seen in both the c-axis conductivity and the ab-plane scattering rate in the sam e doping and tem perature region, suggesting that the two phenom ena are closely related.⁷ R ecent c-axis optical results on single crystals of of slightly underdoped $La_{1:86}Sr_{0:14}CuO_4^{11}$ show that the pseudogap state in the c-axis direction of this material is not as well

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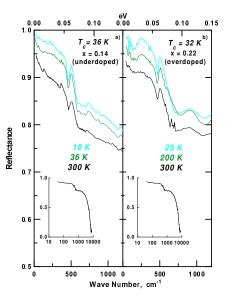


FIG.1. The temperature dependence of the in-plane resistivity of $La_{1:86}Sr_{0:14}CuO_4$ is shown with a sharp superconducting transition at 36 K. The shape of the curve is consistent with T being greater than 300 K.

de ned as it is in the two plane materials. However, as the doping is reduced further the c-axis pseudogap state features become clearer below 0.1 eV.¹²

The weak pseudogap as seen by NMR and neutron scattering¹³ in LSCO has led to the suggestion that the existence of the pseudogap in the spin excitation spectrum is only possible in bilayer compounds such as Y 123 and Y 124. In particular, M illis and M onien attribute the pseudogap (or the spin gap) to strong antiferrom agnetic correlations between the planes in the bilayer, which are responsible for a quantum order-disorder transition.⁴ H owever, the characteristic deviations below the linear extrapolation and T seen in dc conductivity in the bilayer¹⁴ m aterials are also seen in LSCO.¹⁴ Thus, it is important to see if the characteristic depression of the frequency dependent scattering rate in the pseudogap state, seen in the bilayer m aterials such as LSCO.

P revious work on the inplane far infrared optical properties of the single layer lanthanum strontium cuprate includes work on the oxygen doped La_2CuO_4 ¹⁵, thin lm s of LSC O¹⁶ as well as single crystal work at room

tem perature¹⁴. To our know ledge, a study of the tem – perature and doping dependence has not been done. We

ll this gap here by perform ing opticalm easurem ents on high-quality LSCO single crystals at tem peratures ranging from 10 K to 300 K at two di erent doping levels.

To better display the e ect of increased coherence resulting from the formation of the pseudogap state, a memory function, or extended D rude analysis is used.

FIG. 2. The relectance of $La_{1:86}Sr_{0:14}CuO_4$ (a) and $La_{1:78}Sr_{0:22}CuO_4$ (b) is shown at three tem peratures: 10 K, 36 K and 300 K. The thickness of the line goes up as the tem perature goes down. Phonon peaks are visible at 150, 300 and 500 cm⁻¹. The insert in the left panel is a sem i-log graph of the relectance at 300 K which shows a plasm a edge around 7000 cm⁻¹.

In this treatment the complex optical conductivity is modeled by a D rude peak with a frequency-dependent scattering rate and an elective electron mass.^{17;18} W hile the optical conductivity tends to emphasize free particle behaviour, a study of the frequency dependence of the elective scattering rate puts more weight on displaying the interactions of the free particles with the elementary excitations of the system .¹⁹ The temperature evolution of the frequency dependent scattering rate and elective mass spectra are of particular interest and are delended as follow s:

$$1 = (!;T) = \frac{!_{p}^{2}}{4} \operatorname{Re}(\frac{1}{(!;T)})$$
(1)

$$\frac{m (!;T)}{m_{e}} = \frac{1}{!} \frac{!_{p}^{2}}{4} \text{Im} \left(\frac{1}{(!;T)}\right)$$
(2)

Here, $(!;T) = _1(!;T) + i_2(!;T)$ is the complex optical conductivity and $!_p$ is the plasm a frequency of charge carriers.

The single crystals of $La_{2 \times} Sr_x CuO_4$ with approximate dimensions $5x3x3 \text{ mm}^3$ were grown by the travelling-solvent oating zone technique at O ak R idgé⁰ in the case of x = 0.14 and in Tokyo²¹ in the case of x = 0.22. The critical temperature was determined by both SQUID m agnetization and resistivity measurements

and was found to be 36 K for the nom inal concentration of Sr x = 0.14 and 32 K for x = 0.22. Since the highest T_c in the LSCO system has been found at to be 40 K x = 0.17, we conclude that the x = 0.14 crystal is underdoped and the x = 0.22 is overdoped. The crystal with x = 0.14 was aligned using Laue di raction and polished parallel to the CuO₂ planes. The crystal with x = 0.22 was polished in Tokyo in the direction of the ab-plane. It is in portant to have the sam ple surface accurately parallel to the ab-plane to avoid any c-axis contribution to the optical conductivity.²² The m iscut of the sam ple o the ab-plane was checked by a high precision triple axis x-ray di ractom eter and was determ ined to be less than 0.8%.

All re ectivity measurements were performed with a M ichelson interferometer using three dierent detectors which cover frequencies ranging from 10 to 10000 cm¹. The experimental uncertainty in the restance data does not exceed 1%. The dc resistivity measurements were carried out using a standard 4-probe technique.

The result of the resistivity measurement on the $La_{1:86}Sr_{0:14}CuO_4$ single crystal, used in the optical measurements, is shown in Fig. 1. It is commonly accepted that the dc resistivity is linear at high temperatures for LSCO and that the pseudogap begins to form near the temperature where the resistivity drops below this linear trend.¹ At lower temperatures there is a region of superliner temperature dependent resistivity. The T value for our samples with x = 0.14 and x = 0.22, extracted from the phase diagram of Batlogg et al.¹ are 450 K and 200 K, respectively. In agreement with this, the resistivity shows a superlinear temperature dependence below room temperature as expected in the pseudogap region.

In Fig.2 we present the re ectivity data at tem peratures above and below $T_{\rm c}$. For clarity, only three tem peratures are shown: T = 300 K, a tem perature just above the superconducting transition and a low tem perature

10 K or 25 K for x = 0:14 and x = 0:22, respectively, in the superconducting state. In the frequency region shown the re ectance is strongly temperature dependent for both m aterials, dropping by approximately 10% as temperature is increased from the lowest temperature to T = 300 K. The plasma edge is observed at 7800 cm⁻¹ (see insert of Fig.2). The distinct peaks at approximately 150, 300 and 500 cm⁻¹ in the LSCO re ectivity spectra correspond to the excitation of ab-plane TO phonons.²³

The complex optical conductivity (!) was obtained by K ramers-K ronig analysis of the rejectivity data. Since, in principle, this analysis requires knowledge of the rejectance at all frequencies, rejectivity extensions must be used at high and low frequencies. The Hagen-Rubens formula was used for the low frequency rejectivity extrapolation, with parameters taken from the dc resistivity measurements on the same sample shown in Fig. 1 and the results of H. Takagi et al.²⁴ for the overdoped sample. For the high-frequency extension with ! > 8000 cm⁻¹ we used rejectivity results of U chida et al.¹⁴ At frequencies higher than 40 eV the rejectivity was

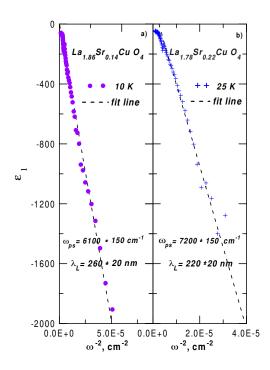


FIG.3. The realpart of the dielectric function as a function of ! 2 of La_{1:86}Sr_{0:14}CuO₄ at 10 K in the panel a) and of La_{1:78}Sr_{0:22}CuO₄ at 25 K at the panel b). The dash line is linear t. The slope of the t gives the values of both a superconducting plasm a frequency of LSCO and the London penetration depth.

assumed to fall as $1=!^4$.

We calculate the plasma frequency of the superconducting charge carriers and the London penetration depth using the following form ula: 26

$$_{1} = 1 \quad \frac{!_{ps}^{2}}{!^{2}}:$$
 (3)

The slope of the low-frequency dielectric function, $_1$ (!), plotted as a function of w $^2\,$ in Fig. 3a,b gives plasm a frequencies of 6100 cm $^1\,$ and 7200 cm $^1\,$ in the superconducting state. The corresponding London penetration depths are $_L$ = 1=2 ! $_{\rm ps}$ = 250 nm and 220 nm for La_{1:86}Sr_{0:14}CuO₄ and La_{1:78}Sr_{0:22}CuO₄, respectively. These values are in good agreement with those obtained previously by Gao et al. in $\,\rm lm\,s^{16}$ ($_L$ = 275 5 nm) and by muon-spin-relaxation 25 ($_L$ = 250 nm).

The real part of the conductivity for the two materials is shown in Fig. 4a,b. For completeness we also show the imaginary part of the conductivity in Fig. 4c,d. The real part of the conductivity has a D rude peak which narrows as the temperature decreases in agreement with the metallic temperature dependence of the dc resistivity. The conductivity of LSCO is temperature-dependent in the M IR frequency region as well. This temperature dependence becomes stronger as $T_{\rm c}$ is reduced by overdoping. There are strong deviations from the D nude shape in the form of an onset or a step in the conductivity at 700 cm 1 . Unlike the Y123, Y124, and B $_{\rm 2}\,\rm Sr_2\,C\,aC\,u_2O_{\,8+}$ (Bi2212) materials which show similar features only at low temperature, the optical conductivity of $\rm La_{1:86}Sr_{0:14}C\,uO_4$ shows a threshold at about 700 cm 1 already at room temperature.

A nother deviation from the D rude form is a shift of the D rude peak from zero frequency to 150 cm⁻¹. This peak grows in m agnitude and narrows as the doping level of Sr increases. A similar peculiarity was observed in the conductivity of a single crystal of La₂CuO₄₊⁻¹⁵; how - ever, it was absent in the optical data of La₂ x Sr_xCuO₄ thin lm s^{1.6}. The nature of the peak is unclear. It is seen in m any HTSC systems and has been attributed to localization.²⁷ An artifact of the polished surface is another possible explanation.

We de ne an overall plasma frequency in terms of the sum nule $w_p^2 = 8 = \int_0^{R_{1m}} \frac{1}{1} (!) d!$ with $!_{max} = 8000$ cm¹. At room temperature, $w_p = 15100$ cm¹ and 13800 cm¹ for LSCO with x = 0.14 and x = 0.22, respectively. These numbers are similar to those measured previously^{16;28;15} and were used to calculate the frequency-dependent scattering rate using Eq. 1. In a recent survey on a number of compounds, Puchkov et al.⁹ found that while the plasma frequency grows with doping in the underdoped region, this growth stops at optimal doping. In agreement, we observe here a slight drop in the spectral weight as one moves from the slightly underdoped to the overdoped region.

The frequency dependent scattering rate and the effective mass are shown in Fig. 5. The spectra can conveniently be divided into two regions. In the high frequency region, starting at about 700 cm 1 , the scattering rate varies linearly with frequency while in the low frequency region there is a clear suppression of 1/ (!,T) below this linear trend. We will call this frequency region of suppressed scattering the pseudogap state region. As the tem perature is low ered this suppression becomes deeper. The dashed lines in Fig 5 are extrapolations of the high frequency linear behaviour to zero frequency. A pseudogap state can be de ned in terms of this suppression of scattering: the material is in the pseudogap state when the scattering rate falls below the high frequency straight-line extrapolation. In the low frequency lim it the scattering rate is proportional to the dc resistivity. Due to this, the 1/ (!,T) suppression should be com pared to the suppression of $_{\rm D\ C}$ (T) 1 at tem peratures below the linear T dependence region. The IR measurem ent gives us the possibility to see both the frequency and the tem perature dependence of this feature.

The temperature dependence above 700 cm 1 is strongly in uenced by the level of Sr doping. In the underdoped sample the high frequency scattering rate is nearly temperature independent. In contrast, the overdoped samples scattering rate above 700 cm 1 increases uniform ly with temperature. The curves are seen to be displaced parallel to each other as the temperature is increased. This behaviour is also seen in other overdoped HTSC 29

To emphasize the di erence between the underdoped and overdoped regimes we tted the high frequency scattering rate curves with a linear function $\frac{1}{(!)} = ! + .$ The values of the and parameters can be found in Table 1. The zero-frequency intercept, , changes only by 7% in the case of underdoped sample but nearly doubles in the overdoped sample between the superconducting transition and 300 K.W hile increases with doping, is substantially smaller in the overdoped sample. The behavior of the intercept is consistent with the other HTSC materials²⁹ but not the slope. Puchkov et al. found that

decreased with doping in most materials. The magnitudes of and of LSCO seem to be substantially lower than those of Y 123, Y 124, B i2212 and T 12202.²⁹

We found that for $La_{1:78}Sr_{0:22}CuO_4$ (the overdoped sam ple) T (300 K) is an order of m agnitude higher than the superconducting transition tem perature $T_{\rm c}$ (32) K). This is signicantly di erent than previous results on overdoped cuprates. Theoretical considerations have led to the suggestion that T coincides with the tem perature of the superconducting transition at the optim aldoping level.^{30;31} This seems to apply to Y 123 and Y 124 where the T and T_c curves cross near the optim aldoping level, but this is clearly not the case here. A detailed exam ination of the scattering rate curves in Fig. 5b suggests that in overdoped sample the suppression of the scattering disappears near room temperature implying that T for x = 0.22 is close to 300 K. This result is consistent with the phase diagram based on the data from transport properties.1

In addition to the pseudogap depth and temperature dependence, several other features of Figs. 5 a,b should be mentioned. The position of the pseudogap remains at 700 cm⁻¹ for all temperatures. There are also several peaks positioned at 1000 cm⁻¹ in scattering rate which complicate the analysis, particularly in the case of the overdoped sam ples. These peaks have been attributed to polaronic e ects^{32;33}

For completeness we plot the elective mass of underdoped sample (Fig. 5c) and the overdoped sample (Fig. 5d). As expected, $\frac{m_{e}(!)}{m_{e}}$ rises to a maximum value between 2 and 5 in the region of the scattering rate suppression. The enhancement of the elective mass in the pseudogap state as well as the upper limit of $\frac{m_{e}(!)}{m_{e}}$ are similar to what has been previously reported for values Y 123, Y 124 and B i2212.²⁹

Before closing we com pare our results with data of G ao et al.¹⁶ on La_{2 x} Sr_xCuO₄₊ Im s and Quijada et al.¹⁵ on oxygen doped La₂CuO₄₊ . Our results in the underdoped case are com parable with those of the oxygen doped m aterial, although Quijada et al. did not carry out

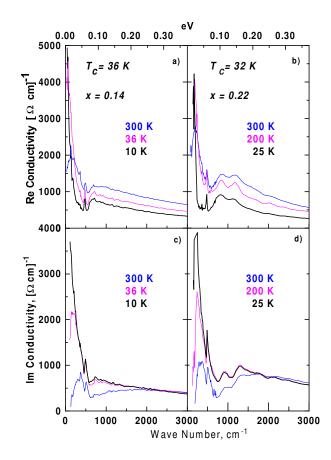


FIG.4. The tem perature dependence of the in-plane conductivity of underdoped $La_{1:86}Sr_{0:14}CuO_4$ (left panel) and overdoped $La_{1:78}Sr_{0:22}CuO_4$ (right panel) are shown. The real part of conductivity (a,b) is suppressed below 700 cm⁻¹. The D rude-like peak forms at room tem perature and narrows as T decreases. The imaginary part of the conductivity is shown on the lower panel (c,d). This line is room tem perature and thick line represents a tem perature below superconducting transition.

TABLE I. Linear t parameters to the scattering rate of La $_2$ $_{\rm X}$ Sr_xCuO $_4$

Sr content	T _c	Т		
		300 K	0.32	1578
x= 0.14	36 K	36 K	0.44	1467
		10 K	0.44	1467
		300 K	0.39	1260
x= 0.22	32 K	200 K	0.5	828
		25 K	0.61	721

a frequency dependent scattering rate analysis for their underdoped sample. The lm results of G ao et al. are quite di erent from our ndings. The lm s used in that study had a strontium level that would correspond to optim al doping in crystals. However, the 1= (!) curves deviatem arkedly from what we observe for slightly under and overdoped samples. The authors perform ed an extended D rude analysis and found a strongly tem perature dependent scattering rate. This is in sharp contrast to our results which would suggest a very weak tem perature dependence. B ased on our work, their sam ples should be in the pseudogap state since they have an x value near optim aldoping. C om paring these results with other systems, in particular with T 12202, two factors suggest the possibility that the $\[m \ s \ m \ ay be overdoped. F \ inst, their T_c was near 30 K, lower than that expected for optimal doping. Secondly, it is known that the oxygen level in <math display="inline">\[m \ s \ can \ vary \ substatially \ and \ in LSCO \ oxygen \ can have a m a jor in uence on the doping level⁴. On the other hand, we cannot com pletely rule out the possibility that all of the crystal results are a ected by the polishing process, and that the <math display="inline">\[m \ s \ better \ represent \ the bulk m \ aterial. It is clearly in portant to m easure <math display="inline">\[m \ s \ where the oxygen \ content \ is controlled by selective \ annealing.$

In conclusion, the optical data in the far-infrared region, taken on two single-layered high- T_c superconductors, shows clear evidence of a pseudogap state in the scattering rate. This pseudogap state extends to higher temperatures than that observed in the multi-layered underdoped cuprates such as YBCO and BSCO.P reviously, the pseudogap state feature with T > T_c was only observed in the underdoped system. In the case of LSCO this feature can be observed in the overdoped regime at a temperature substantially above the superconducting

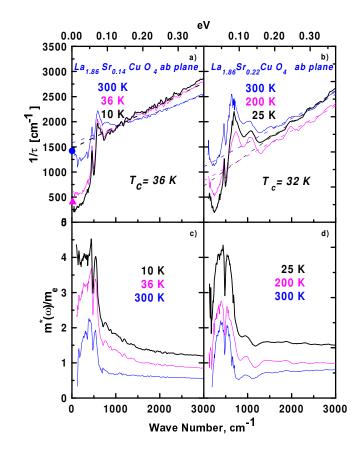


FIG.5. Top panel: the frequency dependent scattering rate of $La_{1:86} Sr_{0:14} CuO_4$ (a) and $La_{1:78} Sr_{0:22} CuO_4$ (b) is calculated using Equation (1). The onset of the suppression in a conductivity corresponds to a drastic change in the frequency dependence of the scattering rate. Above 700 cm⁻¹ the scattering rate is nearly temperature independent and has a linear frequency dependence in the underdoped sample and temperature dependence in the overdoped sample. The dashed lines are linear ts to the scattering rate above 700 cm⁻¹. Below this frequency the scattering rate varies as !¹⁺ and shows a strong temperature dependence. Points on 1= -axis (a) at != 0 corresponds to the DC-value calculated from the resistivity shown in Fig. 1. Bottom panel: The elective mass of underdoped a) and overdoped b) samples is calculated using Equation (2). The onset of enhancement of $\frac{m}{m_e}$ (!) corresponds to the onset of the suppression of the scattering rate. The thinnest line corresponds to higher temperature.

transition tem perature. This suggests that the crossover from the underdoped to the overdoped regime does not suppress T below T_c . The scattering rate is similar for both systems in the pseudogap state. At low frequencies, ! 700 cm⁻¹, the scattering rates are tem perature dependent and change with frequency in a non-linear fashion. Above 700 cm⁻¹ this behaviour becomes linear. W ithin experimental uncertainty the observed high frequency scattering rate of the underdoped sample is not a ected by tem perature.

W e would like to thank JD.G arrett for help in aligning the sample and also PC.M ason, M.Lum sden and BD.G aulin for determining the miscut angle of the underdoped LSCO crystal. We also take this opportunity to thank KC.Irw in and JG.N aeini for the useful collaboration.This work was supported by the N atural Sciences and Engineering R esearch C ouncil of C anada and The C anadian Institute for A dvanced R esearch.

- ¹ B.Batlogg, H.Y.Hwang, H.Takagi, R.J.Cava, H.L.Kao, and J.Kuo, Physica C,235-240, 130 (1994).
- ² H.Y. Hwang, B. Batlogg, H. Tagaki, H.L. Kao, J. Kwo, R.J. Cava, and J.J. Krajewski, Phys. Rev. Lett., 72, 2636 (1994).
- ³ S.K. Tolpygo, J.Y. Lin, M.G irvich, S.Y. Hou, and Julia M.Phillips, Phys. Rev. B, 53, 12454 (1996).
- ⁴ A J. M illis and H. M onien, Phys. Rev. Lett., 70, 2810 (1993).
- ⁵ D S.M arshall, A G. Loeser, Z.-X. Chen, and D S.D essau, Physica C,263,208 (1999).
- ⁶ JW .Loram, K A.M irza, JR.Cooper, and W Y.Liang, Phys.Rev.Lett., 71, 1740 (1993).
- ⁷ D N. Basov, R. Liang, B. Dabrowski, D A. Bonn, W N.Hardy, and T.Timusk, Phys.Rev.Lett., 77, 4090 (1996).
- ⁸ A.V. Puchkov, P.Foumier, D.N. Basov, T.Timusk, A.Kapitulnik, and N.N. Kolesnikov, Phys. Rev. Lett., 77, 3212 (1996).
- ⁹ A.V. Puchkov, P. Fournier, T.Timusk, and N.N.Kolesnikov, Phys. Rev. Lett., 77, 1853 (1996).
- ¹⁰ C.C. Homes, T. Timusk, R. Liang, D.A. Bonn, and W.N. Hardy, Phys. Rev. Lett., 71, 1645 (1993).
- ¹¹ D N. Basov, R. Liang, B. Dabrowski, D A. Bonn and W N. Hardy, T. Timusk, Phys. Rev B, 52, R13141 (1995).
- ¹² S.U chida, K. Tam asaky, and S. Tajim a, Phys. Rev B, 53, 14558 (1996).
- ¹³ T E.M ason, G.Aeppli, and H A.M ook, Phys. Rev. Lett., 68, 1414 (1992).
- ¹⁴ S. Uchida, I. Ido, H. Takagi, T. Arima, Y. Tokura, and S. Tajima, Phys. Rev. B, 43, 7942 (1991).
- ¹⁵ M A.Quijada, D B.Tanner, F C.Chou, D C.Johnston and S.W.Cheong, Phys. Rev. B, 52, 15485 (1995).
- ¹⁶ F. Gao, D.B. Romero, B.D. Tanner, J. Talvacchio, and

- M G.Forrester, Phys. Rev B, 47, 1036 (1993).
- 17 W .G otze and P.W ol e, Phys.Rev.B, 6, 1226 (1972).
- ¹⁸ P.B.Allen, Phys. Rev.B, 3,305 (1971).
- ¹⁹ A. Gold, S.J. Allen, B.A. W ilson and D.C. Tsui, Phys. Rev.B, 25, 3519 (1982).
- ²⁰ S.W. Cheng, G.Aeppli, T.E.Mason, H.Mook, S.M.Hayden, P.C. Can eld, Z.Fisk, K.N. Clausen, and JL.Martinez, Phys. Rev. Lett., 67, 1791 (1991).
- ²¹ T. Kimura, K. Kishio, T. Kobayashi, Y. Nakayama, N. Motohira, K. Kitazawa, and K. Yamafuji, Physica C (Am sterdam), 192, 247 (1992).
- ²² J.O renstein and D.H.Rapkine, Phys. Rev. Lett., 60, 968 (1988).
- ²³ S. Tajima, S. Uchida, S. Ishibashi, T. Ido and H. Takagi, T. Arima and Y. Tokura, Physica C, 168, 117 (1990).
- ²⁴ H. Takagi, B. Batlogg, H L. Kao, J. Kwo, R J. Cava, J.J. Krajewski, and W F. Peck, Jr., Phys. Rev. Lett., 69, 2975 (1992).
- ²⁵ G.Aeppli, R.J.Cava, E.J.Ansaldo, J.H.Brewer, S.R.K reitzm an, G.M. Luke, D.R. Noakes, and R.F.Kie, Phys. Rev.B, 35, 7129 (1987).
- ²⁶ D B.Tanner and T.T in usk, in Physical Properties of H igh Tem perature Superconductors I, edited by D M.G insberg (word Scienti c, Singapure, 1992), p.363.
- ²⁷ T. Timusk, D.N. Basov, C.C. Homes, A.V. Puchkov, and M. Reedyk, Journ. of Superconductivity, 8, 437 (1995).
- ²⁸ K. Tam asaku, T. Itoh, H. Takagi, and S. Uchida, Phys. Rev. Lett., 72, 3088 (1994)
- ²⁹ A.V.Puchkov, D.N.Basov, and T.Timusk, J.Phys.: Condens.M atter, 8, 10049 (1996).
- ³⁰ P.A. Lee and N. Nagaosa, Phys. Rev. B, 46, 5621 (1992).
- ³¹ V J. Em ery and S A . K ivelson, P hys. R ev. Lett., 74, 3253 (1995).
- ³² Y. Yagil and E.K.H. Salje, Physica C, 235-140, 1143 (1994).
- ³³ G A. Thom as, D H. Rapkine, S L. Cooper, S.-W. Cheong, A S. Cooper, L S. Schneem eyer, and J.V. Waszczak, Phys. Rev. B, 45, 2474 (1992).
- ³⁴ H. Zhang, H. Sato, and G.L. Liedl, Physica C 234, 185, (1994).